

# Theory of the Atomic and Electronic Structure of DXCen

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Effect of local alloy disorder on emission kinetics of deep donors (DXcenters) in Al <sub>x</sub> Ga <sub>1-x</sub> As of low Al content. Applied Physics Letters, 1988, 53, 2546-2548.	3.3	104
2	Electron trapping by metastable effective-mass states of DXdonors in indirect-band-gap Al <sub>x</sub> Ga <sub>1-x</sub> As:Te. Physical Review B, 1989, 40, 9671-9682.	3.2	68
3	Hydrogen bonding and diffusion in crystalline silicon. Physical Review B, 1989, 40, 11644-11653.	3.2	172
4	Donors in semiconductors and metastability. Physical Review B, 1989, 40, 10006-10008.	3.2	10
5	Pressure dependence of DXcenter mobility in highly doped GaAs. Applied Physics Letters, 1989, 55, 1409-1411.	3.3	58
6	Comparative photoluminescence study of hydrogenation of GaAs, Al <sub>x</sub> Ga <sub>1-x</sub> As, and AlAs. Applied Physics Letters, 1989, 55, 475-477.	3.3	18
7	Chadi, Chang, and Walukiewicz reply. Physical Review Letters, 1989, 62, 1923-1923.	7.8	24
8	Photoluminescence transients due to hole capture at DXcenters in Al <sub>x</sub> Ga <sub>1-x</sub> As:Si. Physical Review Letters, 1989, 63, 2276-2279.	7.8	50
9	Symmetry of the Si shallow donor state in AlAs/GaAs and Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs heterostructures. Physical Review B, 1989, 40, 3447-3450.	3.2	28
10	Electron-paramagnetic-resonance measurements of Si-donor-related levels in Al <sub>x</sub> Ga <sub>1-x</sub> As. Physical Review B, 1989, 39, 5554-5557.	3.2	63
11	DXcenter in Ga <sub>1-x</sub> Al <sub>x</sub> As alloys. Physical Review B, 1989, 40, 7663-7670.	3.2	46
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13	Isolated arsenic-antisite defect in GaAs and the properties of EL2. Physical Review B, 1989, 40, 10391-10401.	3.2	172
14	Comment on "Physical meaning of electron capture kinetics on DXcenters" [Appl. Phys. Lett. 53, 1841 (1988)]. Applied Physics Letters, 1989, 55, 804-805.	3.3	4
15	Application of the Williams-Watts decay law to DXcenter capture and emission kinetics. Applied Physics Letters, 1989, 54, 445-447.	3.3	29
16	Evidence against the negative-charge-state model for the DXcenter in n-type GaAs. Physical Review Letters, 1989, 62, 1922-1922.	7.8	48
17	Discovery of a new photoinduced electron trap state shallower than the DX center in Si doped Al <sub>x</sub> Ga <sub>1-x</sub> As. Journal of Applied Physics, 1989, 66, 5632-5634.	2.5	26
18	Magnetic studies of persistent photoconductivity in Al <sub>x</sub> Ga <sub>1-x</sub> As. Physical Review Letters, 1989, 63, 1311-1314.	7.8	75

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19	Conduction band structure dependence of persistent photoconductivity in Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> As studied by Hall measurements under hydrostatic pressure. Applied Physics Letters, 1989, 55, 1124-1126.	3.3	10
20	Pressure dependence of the Pb center at the Si/SiO <sub>2</sub> interface. Physical Review B, 1989, 39, 3431-3434.	3.2	6
21	Influence of the DX center on the capacitance-voltage characteristics of $\Gamma$ -doped GaAs. Applied Physics Letters, 1989, 55, 156-158.	3.3	20
22	Electron-paramagnetic-resonance study of the Sn DX center in direct-gap Ga <sub>0.69</sub> Al <sub>0.31</sub> As. Physical Review B, 1989, 40, 5892-5895.	3.2	42
23	Pressure dependence of the DX center in Ga <sub>1-x</sub> Al <sub>x</sub> As:Te. Physical Review B, 1989, 40, 7831-7838.	3.2	28
24	Negative-U property of the DX center in Al <sub>x</sub> Ga <sub>1-x</sub> As:Si. Physical Review B, 1989, 40, 1430-1433.	3.2	22
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38	The DX Center: Evidence for Charge Capture Via an Excited Intermediate State. Materials Research Society Symposia Proceedings, 1989, 163, 729.	0.1	26
39	EPR Studies of DX Center Related Paramagnetic States in Ga <sub>0.69</sub> Al <sub>0.31</sub> As:Sn. Materials Research Society Symposia Proceedings, 1989, 148, 439.	0.1	1
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54	Deep donor levels in Te-Doped GaAsP alloy. Chinese Physics Letters, 1990, 7, 129-132.	3.3	3

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56	Lattice-distortion-induced electronic bistability of the donor defect in semiconductors. <i>Physical Review B</i> , 1990, 41, 8323-8332.	3.2	3
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62	Relaxation of stored charge carriers in a Zn <sub>0.3</sub> Cd <sub>0.7</sub> Se mixed crystal. <i>Physical Review B</i> , 1990, 41, 5178-5187.	3.2	34
63	Electric-field-enhanced electron emission from isolated sulfur and selenium donors in silicon. <i>Physical Review B</i> , 1990, 42, 1381-1387.	3.2	15
64	Donor states in GaAs under hydrostatic pressure. <i>Physical Review B</i> , 1990, 42, 11791-11800.	3.2	16
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66	Stability of DX centers in Al <sub>x</sub> Ga <sub>1-x</sub> As alloys. <i>Physical Review B</i> , 1990, 42, 7174-7177.	3.2	71
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68	Relaxation of persistent photoconductivity in Al <sub>0.3</sub> Ga <sub>0.7</sub> As. <i>Physical Review B</i> , 1990, 42, 5855-5858.	3.2	88
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